# 2SD1994, 2SD1994A

## Silicon NPN Epitaxial Planar Type

For low-frequency power amplification and drive Complementary pair with 2SB1322 and 2SB1322A

#### **■** Features

- •Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- •2-3W output can be obtained in a complementary pair with 2SB1322 and 2SB1322A.
- •Automatic insertion by radial taping possible

## ■ Absolute Maximum Ratings (Ta=25°C)

| Item                         |          | Symbol           | Value    | Unit          |  |
|------------------------------|----------|------------------|----------|---------------|--|
| Collector-Base               | 2SD1994  |                  | 30       | V             |  |
| Voltage                      | 2SD1994A | V <sub>CBO</sub> | 60       | <u> </u>      |  |
| Collector-Emitter<br>Voltage | 2SD1994  |                  | 25       | V             |  |
|                              | 2SD1994A | $V_{CEO}$        | 50       | · · · ·       |  |
| Collector-Base Voltage       |          | V <sub>EBO</sub> | 5        | , *: <b>V</b> |  |
| Peak Collector Current       |          | I <sub>CP</sub>  | 1.5      | Α .           |  |
| Collector Current            |          | Ic               | 1        | A C           |  |
| Collector Power Dissipation  |          | Pc*              | 1        | W W           |  |
| Junction Temperature         |          | Ti               | 150      | C             |  |
| Storage Temperature          |          | T <sub>stg</sub> | -55~+150 | 20 CC         |  |

<sup>\*</sup>Copper foil on PCB against Collector: 1.7mm thick, 1cm2 in area

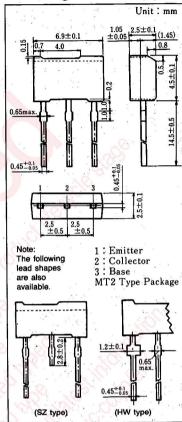
### ■ Electrical Characteristics (Ta=25°C)

| Item                                |          | Symbol                | Condition   | min. | typ.  | max. | Unit |
|-------------------------------------|----------|-----------------------|---|------|-------|------|------|
| Collector Cutoff Cur                | rent     | $I_{CBO}$             | $V_{CB}=20V$ , $I_{E}=0$                                      | 00,  | *.    | 0.1  | μA   |
| Collector-Base                      | 2SD1994  | V <sub>CBO</sub>      | $I_{C}=10 \mu\text{A}, \ I_{E}=0$                             | 30   |       |      | V    |
|                                     | 2SD1994A |                       |   | 60   |       |      |      |
| Collector-Emitter<br>Voltage        | 2SD1994  | V <sub>CEO</sub>      | $I_{C} = 2 \text{ mA}, I_{B} = 0$                             | 25   |       |      | v    |
|                                     | 2SD1994A |                       |   | 50   |       |      |      |
| Emitter-Base Voltage                |          | $I_{EBO}$             | $I_{\rm E} = 10 \mu{\rm A}, \ I_{\rm C} = 0$                  | , 5  |       |      | V    |
| DC Current Gain                     |          | h <sub>FE1</sub> *1   | $V_{CE} = 10V$ , $I_{C} = 500 \text{mA}^{*2}$                 | 85   | 160   | 340  |      |
|                                     |          | h <sub>FE2</sub>      | $V_{CE} = 5 \text{ V}, I_{B} = 1 \text{ A}^{*2}$              | 50   | 100   |      |      |
|                                     |          | V <sub>CE (sat)</sub> | $I_{\rm C} = 500  \rm mA$ , $I_{\rm B} = 50  \rm mA^{*2}$     |      | 0.2   | 0.4  | V    |
|                                     |          | V <sub>BE</sub> (sat) | $I_C = 500 \text{mA}, I_B = 50 \text{mA}^{*2}$                | ā    | 0.85  | 1.2  | V    |
| Transition Frequency f <sub>T</sub> |          |                       | $V_{CB} = 10V$ , $I_E = -50 \text{mA}$ , $f = 200 \text{MHz}$ |      | - 200 |      | MHz  |
| Collector Output Capacitance Cob    |          | Cob                   | $V_{CB} = 10V$ , $I_{E} = 0$ , $f = 1 \text{ MHz}$            |      | 11    | 20   | pF   |

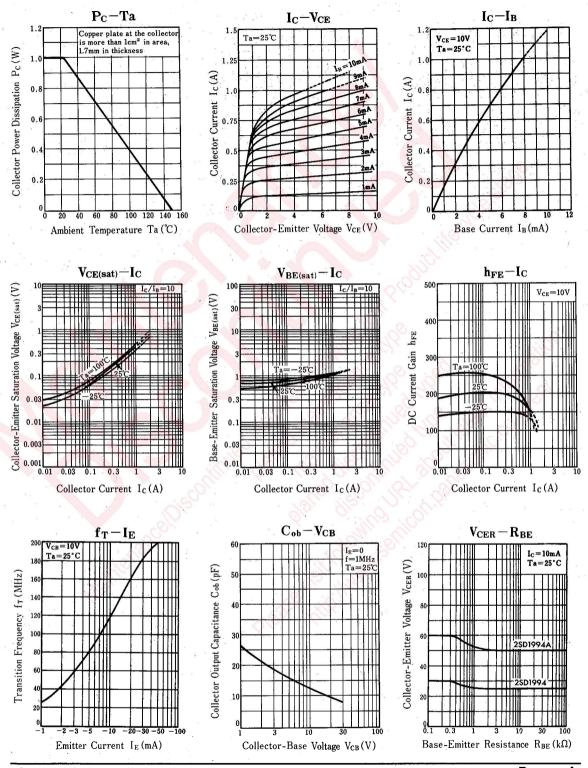
#### \*1h<sub>FE1</sub> Ranking

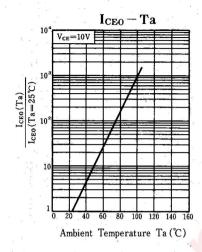
| Rank             | Q      | R       | S       |
|------------------|--------|---------|---------|
| h <sub>FE1</sub> | 85~170 | 120~240 | 170~340 |

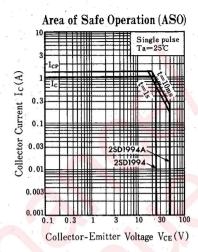
### ■ Package Dimensions



<sup>\*2</sup> Pulse Measurement







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